## Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DZT2907A)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)


## Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish - Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.115 grams (approximate)


SOT-223


TOP VIEW

Schematic and Pin Configuration

Maximum Ratings $@ T_{A}=25^{\circ} \mathrm{C}$ unless otherwise specified

| Characteristic | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Collector-Base Voltage | $\mathrm{V}_{\text {CBO }}$ | 75 | V |
| Collector-Emitter Voltage | $\mathrm{V}_{\text {CEO }}$ | 40 | V |
| Emitter-Base Voltage | $\mathrm{V}_{\text {EBO }}$ | 6 | V |
| Collector Continuous Current | $\mathrm{I}_{\mathrm{C}}$ | 600 | mA |

## Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Power Dissipation @ $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}($ Note 3) | $\mathrm{P}_{\mathrm{d}}$ | 1 | W |
| Thermal Resistance, Junction to Ambient Air (Note 3) $@ \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $\mathrm{R}_{\theta \mathrm{JA}}$ | 125 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Operating and Storage Temperature Range | $\mathrm{T}_{\mathrm{j},} \mathrm{T}_{\mathrm{STG}}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Notes: 1. No purposefully added lead
. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead free/index.php.
3. Device mounted on FR-4 PCB pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

Electrical Characteristics $@ T_{A}=25^{\circ} \mathrm{C}$ unless otherwise specified

| Characteristic | Symbol | Min | Max | Unit | Test Conditions |
| :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS (Note 4) |  |  |  |  |  |
| Collector-Base Breakdown Voltage | $\mathrm{V}_{\text {(BR)CBO }}$ | 75 | - | V | $\mathrm{I}_{\mathrm{C}}=10 \mu \mathrm{~A}, \mathrm{I}_{\mathrm{E}}=0$ |
| Collector-Emitter Breakdown Voltage | $\mathrm{V}_{\text {(BR)CEO }}$ | 40 | - | V | $\mathrm{IC}_{\mathrm{C}}=10 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=0$ |
| Emitter-Base Breakdown Voltage | $V_{(B R) E B O}$ | 6 | - | V | $\mathrm{I}_{\mathrm{E}}=10 \mu \mathrm{~A}, \mathrm{I}_{\mathrm{C}}=0$ |
| Collector Cut-Off Current | Ісво | - | 10 | nA | $\mathrm{V}_{C B}=50 \mathrm{~V}, \mathrm{IE}_{\mathrm{E}}=0$ |
|  |  | - | 10 | $\mu \mathrm{A}$ | $\mathrm{V}_{C B}=50 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0, \mathrm{~T}_{\mathrm{A}}=150^{\circ} \mathrm{C}$ |
| Emitter Cut-Off Current | $\mathrm{I}_{\text {EBO }}$ | - | 10 | nA | $\mathrm{V}_{\mathrm{EB}}=3 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=0$ |
| Collector-Emitter Cut-Off Current | ICEX | - | 10 | nA | $\mathrm{V}_{\text {CE }}=60 \mathrm{~V}, \mathrm{~V}_{\text {EB( }(\text { ffi) }}=3 \mathrm{~V}$ |
| ON CHARACTERISTICS (Note 4) |  |  |  |  |  |
| Collector-Emitter Saturation Voltage | $\mathrm{V}_{\text {CE(SAT) }}$ | - | 0.3 | V | $\mathrm{IC}_{\mathrm{C}}=150 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=15 \mathrm{~mA}$ |
|  |  | - | 1.0 | V | $\mathrm{I}_{\mathrm{C}}=500 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=50 \mathrm{~mA}$ |
| Base-Emitter Saturation Voltage | $V_{\text {be(SAT) }}$ | 0.6 | 1.2 | V | $\mathrm{IC}=150 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=15 \mathrm{~mA}$ |
|  |  | - | 2.0 | V | $\mathrm{IC}_{\mathrm{C}}=500 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=50 \mathrm{~mA}$ |
| DC Current Gain | $h_{\text {FE }}$ | 35 | - | V | $\mathrm{IC}=0.1 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=10 \mathrm{~V}$ |
|  |  | 50 | - |  | $\mathrm{I}_{\mathrm{C}}=1 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=10 \mathrm{~V}$ |
|  |  | 75 | - |  | $\mathrm{IC}=10 \mathrm{~mA}, \mathrm{~V}_{\text {CE }}=10 \mathrm{~V}$ |
|  |  | 35 | - |  | $\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}, \mathrm{~V}_{\text {CE }}=10 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=-55^{\circ} \mathrm{C}$ |
|  |  | 100 | 300 |  | $\mathrm{IC}=150 \mathrm{~mA}, \mathrm{~V}_{\text {CE }}=10 \mathrm{~V}$ |
|  |  | 50 | - |  | $\mathrm{I}_{\mathrm{C}}=150 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=1 \mathrm{~V}$ |
|  |  | 40 | - |  | $\mathrm{I}_{\mathrm{C}}=500 \mathrm{~mA}, \mathrm{~V}_{\text {CE }}=10 \mathrm{~V}$ |
| SMALL SIGNAL CHARACTERISTICS |  |  |  |  |  |
| Transition Frequency | $\mathrm{f}_{\mathrm{T}}$ | 300 | - | MHz | $\mathrm{I}_{\mathrm{C}}=20 \mathrm{~mA}, \mathrm{~V}_{\text {CE }}=20 \mathrm{~V}, \mathrm{f}=100 \mathrm{MHz}$ |
| Output Capacitance | $\mathrm{C}_{\text {obo }}$ | - | 8 | pF | $\mathrm{V}_{C B}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0, \mathrm{f}=1 \mathrm{MHz}$ |
| Input Capacitance | $\mathrm{C}_{\text {ibo }}$ | - | 25 | pF | $\mathrm{V}_{\text {EB }}=0.5 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=0, \mathrm{f}=1 \mathrm{MHz}$ |
| SWITCHING CHARACTERISTICS |  |  |  |  |  |
| Delay Time | $\mathrm{t}_{\text {d }}$ | - | 10 | ns | $\mathrm{V}_{\mathrm{CE}}=30 \mathrm{~V}, \mathrm{~V}_{\mathrm{EB} \text { (off) }}=0.5 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=150 \mathrm{~mA}, \mathrm{I}_{\mathrm{B} 1}=15 \mathrm{~mA}$ |
| Rise Time | $\mathrm{tr}_{\mathrm{r}}$ | - | 25 | ns |  |
| Storage Time | $\mathrm{t}_{\mathrm{s}}$ | - | 225 | ns | $\mathrm{V}_{\mathrm{CE}}=30 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=150 \mathrm{~mA}, \mathrm{I}_{\mathrm{B} 1}=\mathrm{I}_{\mathrm{B} 2}=15 \mathrm{~mA}$ |
| Fall Time | $\mathrm{t}_{\mathrm{f}}$ | - | 60 | ns |  |

Notes: 4. Measured under pulsed conditions. Pulse width $=300 \mu$ S. Duty Cycle, $\mathrm{d}<=2 \%$.


Fig. 1 Power Dissipation vs. Ambient Temperature


Fig. 2 Typical Collector Current
vs. Collector Emitter Voltage


Fig. 3 Typical DC Current Gain vs. Collector Current


Fig. 5 Typical Base Emitter Turn-On Voltage vs. Collector Current


Fig. 7 Typical Capacitance Characteristics


Fig. 4 Typical Collector Emitter Saturation Voltage vs. Collector Current


Fig. 6 Typical Base Emitter Saturation Voltage
vs. Collector Current


Fig. 8 Typical Gain-Bandwidth Product
vs. Collector Current

## Ordering Information (Note 5)

| Device | Packaging | Shipping |
| :---: | :---: | :---: |
| DZT2222A-13 | SOT-223 | 2500/Tape \& Reel |

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## Marking Information



K1P = Product Type Marking Code
YWW = Date Code Marking
$\mathrm{Y}=$ Last Digit of Year ex: 7=2007
WW = Week Code 01-52

## Package Outline Dimensions



| SOT-223 |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
| Dim | Min | Max | Typ |  |
| A | 1.55 | 1.65 | 1.60 |  |
| A1 | 0.010 | 0.15 | 0.05 |  |
| b1 | 2.90 | 3.10 | 3.00 |  |
| b2 | 0.60 | 0.80 | 0.70 |  |
| C | 0.20 | 0.30 | 0.25 |  |
| D | 6.45 | 6.55 | 6.50 |  |
| E | 3.45 | 3.55 | 3.50 |  |
| E1 | 6.90 | 7.10 | 7.00 |  |
| e | - | - | 4.60 |  |
| e1 | - | - | 2.30 |  |
| L | 0.55 | 0.75 | 0.65 |  |
| Q | 0.84 | 0.94 | 0.89 |  |
| All Dimensions in | mm |  |  |  |
|  |  |  |  |  |

## Suggested Pad Layout: (Based on IPC-SM-782)



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